

WHAT IS CLAIMED IS:

Sub 1
1. A semiconductor device comprising:
a semiconductor element bonded on a first metallic
layer;
5 a wire for electrically connecting an electrode pad of
the semiconductor element to a second metallic layer; and
a resin package for sealing said semiconductor element,
wherein rear surfaces of the first metallic layer and the
second metallic layer are flush with a bottom of said resin
10 package.

2. A semiconductor device according to claim 1, wherein the
first metallic layer has a larger area than that of a bottom
surface of the semiconductor element.

3. A semiconductor device according to claim 1, wherein said
15 first metallic layer is thicker than said second metallic layer,
and said first metallic layer has a smaller area than a bottom
area of the semiconductor element.

4. A semiconductor device according to claim 1, wherein said
20 second metallic layer is individually exposed from a bottom of
said resin package.

Sub 2
5. A method of manufacturing a semiconductor device
comprising the steps of:

forming an electrodeposition frame on a flexible flat
metallic substrate, said electrodeposition frame with first
25 metallic layers and second metallic layers for external
extension being patterned;

contiguously mounting a plurality of semiconductor elements each with electrode pads thereon, on said first metallic layers, respectively;

5 wire-bonding the electrode pads to said second metallic layers which are located between said semiconductor elements;

62 resin-sealing said semiconductor elements mounted on said electrodeposition frame;

removing said metallic substrate to provide a resin sealing body; and

10 cutting said resin sealing body into individual semiconductor devices with the aid of cutting marks formed the first and second metallic layers.

6. A method of manufacturing a semiconductor device according to claim 5, further comprising after the step of cutting, the step of:

15 depositing metallic layers for electrodes to the second metallic layers exposed from a rear surface of said resin sealing body.

20 7. A method of manufacturing a semiconductor device according to claim 5, wherein

in said step of cutting of said resin sealing body, it is cut along a center line of each of the second metallic layers to provide metallic layers for external extension for adjacent semiconductor elements.

25 8. A method of manufacturing a semiconductor device

according to claim 5, wherein said electrodeposition frame
is resin sealed together with said semiconductor elements using
said metallic substrate as a lower die.